PRELIMINARY DATASHEET

IGBT Module in iQPak™2 Package
PFC-Boost configuration

- Ultra low loss IGBT
- Highly rugged SPT design
- Pb free finished; RoHS compliant

MAXIMUM RATINGS, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Value	Units
Collector-emitter voltage	V_{CES}	1200	V
DC collector current T_C=80°C	I_C	228	A
Repetitive peak collector current	I_{CRM}	456	
Diode DC forward current T_C=80°C	I_F	200	
Peak forward current	I_{FM}	400	
Gate-emitter peak voltage	V_{GES}	± 20	V
IGBT short circuit SOA V_{CC} =1200V , V_{GE} = 15V, V_{CEM} ≤1200V, T_{VJ} ≤ 125°C	tsc	10	µs
Operating junction and storage temperature	T_j, T_{stg}	-40… +150	°C

Thermal and Isolation Characteristics

Parameter	Symbol	Max. Value	Units
Characteristics			
IGBT thermal resistance, junction to case	R_{thJC}	0.11	K/W
Diode thermal resistance, junction to case	R_{thJCD}	0.16	
Isolation voltage, RMS (measured between terminals and mounting base, 50-60 Hz, for 1-3 seconds)	V_{iso}	3000	V

ELECTRICAL CHARACTERISTICS, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 4mA	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C = 228A V_{GE} = 15V, I_C = 200A	1.7 -	1.87 -	2.0 1.74	
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 200A	-	1.8	2.2	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 8 mA, V_{CE} = V_{GE}	5.0	6.3	7.0	
Zero gate voltage collector current	I_{CES}	V_{CE} = 1200V, V_{GE} = 0 T= 25°C	-	-	400	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = ±20V,	-200	-	200	nA
Internal gate resistance	R_{Gint}		-	2.5	-	Ω

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ELECTRICAL CHARACTERISTICS, at T_j = 25°C, unless otherwise specified

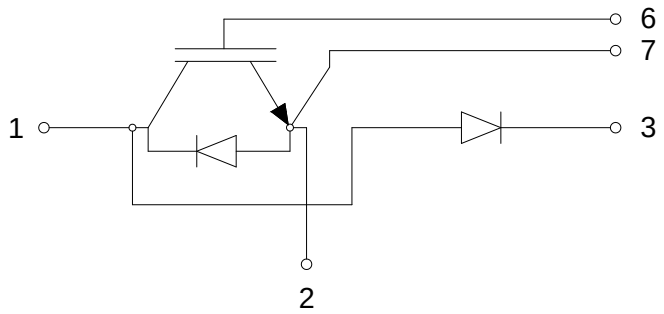
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics						
Gate charge	Q_{ge}	I_C = 228A, V_{CE} = 600V, V_{GE} = ±15V	-	2444	-	nC
Input capacitance	C_{iss}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	17.2	-	nF
Reverse transfer capacitance	C_{rss}		-	1.2	-	
Reverse transfer capacitance	C_{rss}		-	0.8	-	
Short circuit current	I_{SC}	T_C=125 °C , V_{CC}=900V, V_{GE}=15V, t_{psc}≤10μs, V_{CEM}=≤1200V	-	1080	-	A

SWITCHING CHARACTERISTICS, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
IGBT Characteristics						
Turn-on delay time	$t_{d(on)}$	V_{CC}=600V, I_C=228A, V_{GE}=-15V to 18V, R_G=4.5Ω, Inductive load.	-	333	-	ns
Rise time	t_r		-	140	-	
Turn-off delay time	$t_{d(off)}$		-	224	-	
Fall time	t_f		-	115	-	
Turn-ON energy	E_{on}		-	46	-	mJ
Turn-OFF energy	E_{off}		-	13	-	mJ

Anti-Parallel Diode Characteristics, at T_j = 25°C, unless otherwise specified

Diode reverse recovery time	t_{rr}	V_R=600V, I_F=200A di_F/dt = 650A/μs Inductive load	-	618	-	ns
Diode reverse recovery charge	Q_{rr}		-	23	-	μC
Diode peak reverse recovery current	I_{rrm}		-	57	-	A



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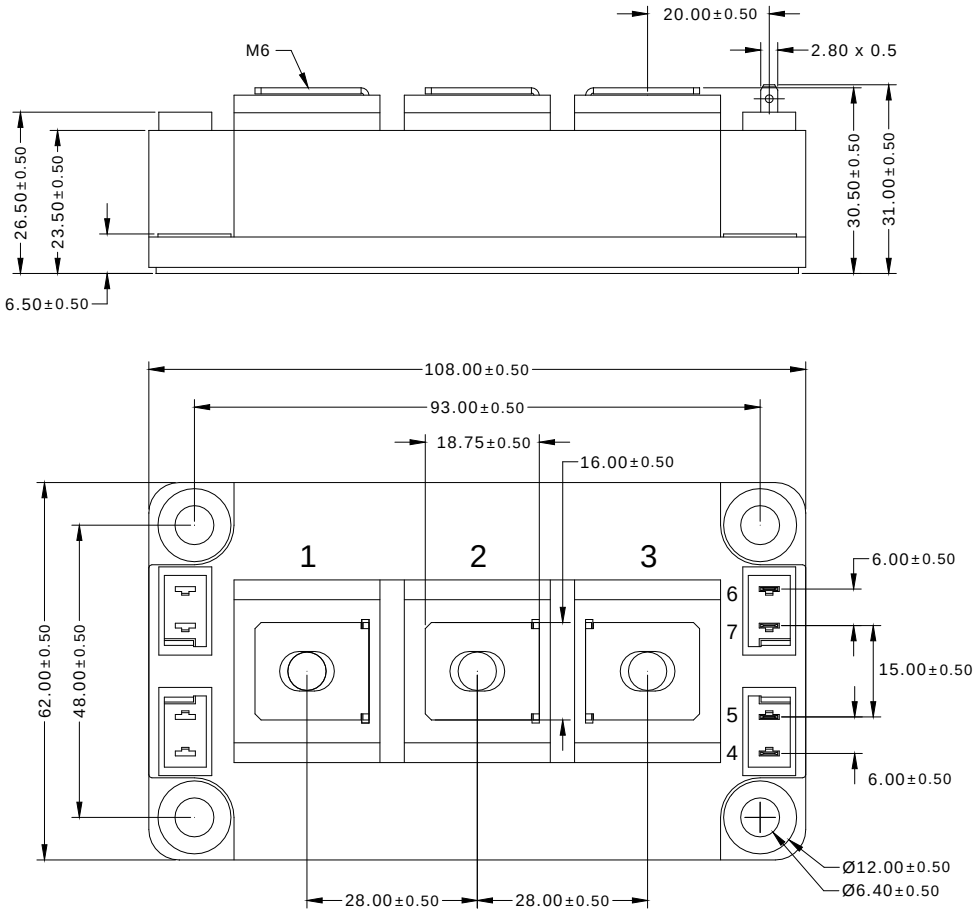
Package Outline Drawing



CAUTION: These devices are ESD sensitive. Use proper handling procedure.

Disclaimer

These specifications may not be considered as a guarantee of components characteristics. Components have to be tested depending on intended application as adjustments may be necessary. The use of **iQXPRZ Power Inc.** components in life support appliances and systems are subject to written approval of **iQXPRZ Power Inc.**

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